



PSMN6R7-40MLD

N-channel 40 V, 6.7 mΩ, logic level MOSFET in LPAK33 using NextPower-S3 technology

14 August 2019

Product data sheet

1. General description

50 A, logic level N-channel enhancement mode MOSFET in 175 °C LPAK33 package using advanced TrenchMOS Superjunction technology. This product has been designed and qualified for high efficiency applications operating at high switching frequencies.

2. Features and benefits

- Avalanche rated, 100% tested
- NextPower-S3 technology delivers 'superfast switching with soft body-diode recovery'
- Low Q_{RR} , Q_G and Q_{GD} for high efficiency, especially at higher switching frequencies
- Low spiking and ringing for low EMI designs
- High reliability clip bond and solder die attach Mini Power SO8 package; no glue, no wire bonds, qualified to 175 °C
- Exposed leads can be wave soldered; visual solder joint inspection and high quality solder joints
- Low parasitic inductance and resistance

3. Applications

- Secondary side synchronous rectification
- DC-to-DC converters
- Brushless DC motor drive
- LED lighting

4. Quick reference data

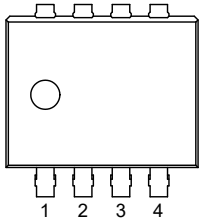
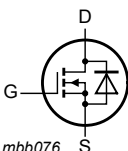
Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	40	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; Fig. 2	[1]	-	-	50	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; Fig. 1		-	-	65	W
T _j	junction temperature			-55	-	175	°C
Static characteristics							
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 15 A; T _j = 25 °C; Fig. 10		-	7	8.6	mΩ
		V _{GS} = 10 V; I _D = 20 A; T _j = 25 °C; Fig. 10		-	5.5	6.7	mΩ
Dynamic characteristics							
Q _{G(tot)}	total gate charge	I _D = 20 A; V _{DS} = 20 V; V _{GS} = 4.5 V; Fig. 12 ; Fig. 13		6.5	10	14	nC
Q _{GD}	gate-drain charge			0.7	2.5	5	nC

[1] 50A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 LPAK33 (SOT1210)	 mbb076
2	S	source		
3	S	source		
4	G	gate		
mb	D	Mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN6R7-40MLD	LPAK33	Plastic, single ended surface mounted package (LPAK33); 8 leads; 0.65 mm pitch	SOT1210

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN6R7-40MLD	6H7L40

8. Limiting values

Table 5. Limiting values

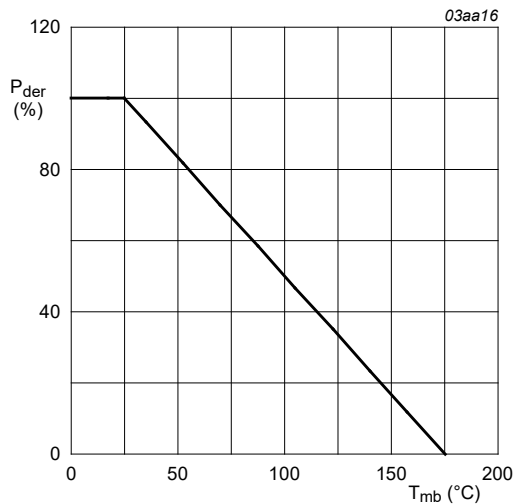
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$		-	40	V
V_{DSM}	peak drain-source voltage	$t_p \leq 20\text{ ns}$; $f \leq 500\text{ kHz}$; $E_{DS(AL)} \leq 200\text{ nJ}$; pulsed		-	45	V
V_{DGR}	drain-gate voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$; $R_{GS} = 20\text{ k}\Omega$		-	40	V
V_{GS}	gate-source voltage			-20	20	V
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Fig. 1		-	65	W
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; Fig. 2	[1]	-	50	A
		$V_{GS} = 10\text{ V}$; $T_{mb} = 100\text{ °C}$; Fig. 2		-	50	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$; Fig. 3		-	282	A
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drain diode						
I_S	source current	$T_{mb} = 25\text{ °C}$		-	50	A

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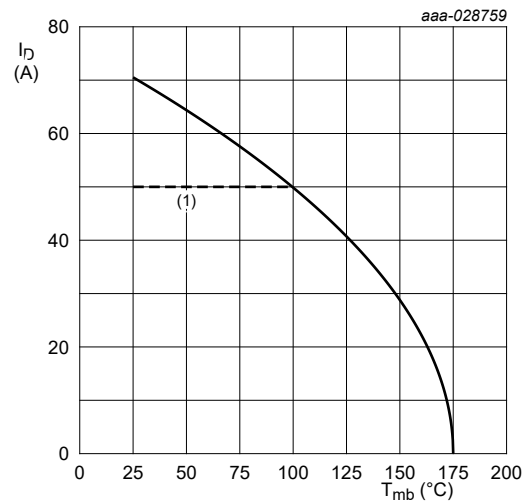
Symbol	Parameter	Conditions		Min	Max	Unit
I_{SM}	peak source current	pulsed; $t_p \leq 10 \mu s$; $T_{mb} = 25^\circ C$		-	282	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 25 A$; $V_{sup} \leq 40 V$; $R_{GS} = 50 \Omega$; $V_{GS} = 10 V$; $T_{j(init)} = 25^\circ C$; unclamped; $t_p = 89.4 \mu s$	[2]	-	58	mJ

- [1] 50A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
 [2] Protected by 100% test



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ C)}} \times 100\%$$

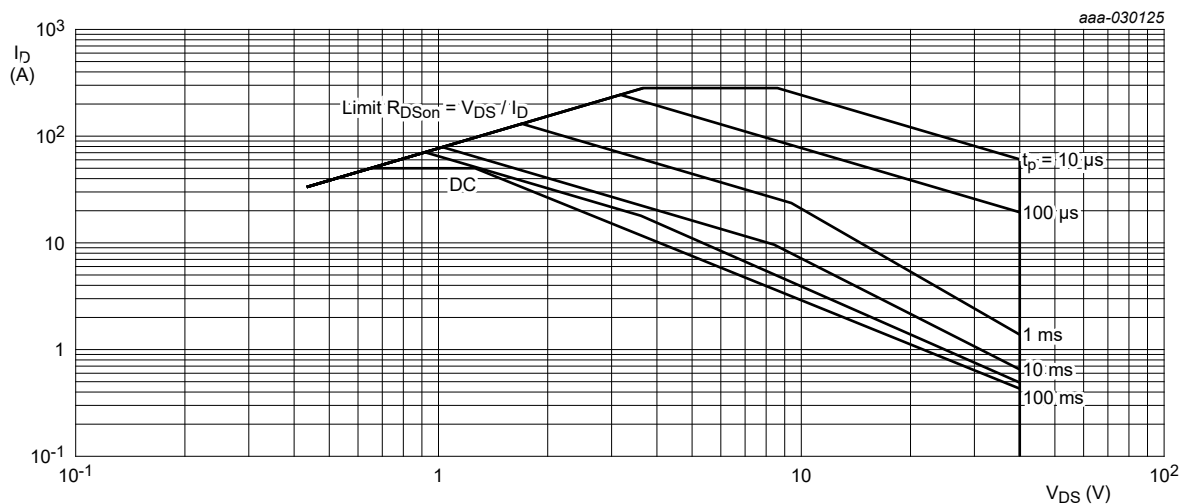
Fig. 1. Normalized total power dissipation as a function of mounting base temperature



$V_{GS} \geq 10 V$

(1) 50A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

Fig. 2. Continuous drain current as a function of mounting base temperature



$T_{mb} = 25^\circ C$; I_{DM} is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 4	-	2.09	2.32	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Fig. 5	-	50	-	K/W
		Fig. 6	-	130	-	K/W

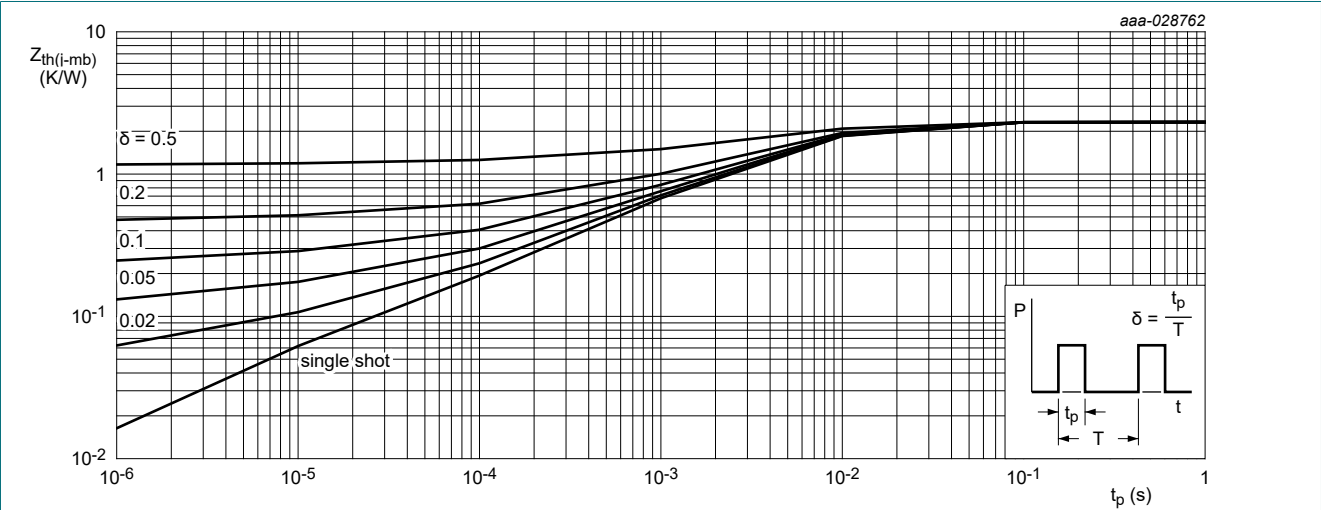


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

aaa-028026

Copper square 25.4 mm square; 70 μm thick on FR4 board

aaa-028025

70 μm thick copper on FR4 board

Fig. 5. PCB layout for resistance from junction to ambient

Fig. 6. PCB layout with minimum footprint for thermal resistance from junction to ambient

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250\text{ }\mu\text{A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^{\circ}\text{C}$	40	-	-	V
		$I_D = 250\text{ }\mu\text{A}; V_{GS} = 0\text{ V}; T_j = -55\text{ }^{\circ}\text{C}$	36	-	-	V

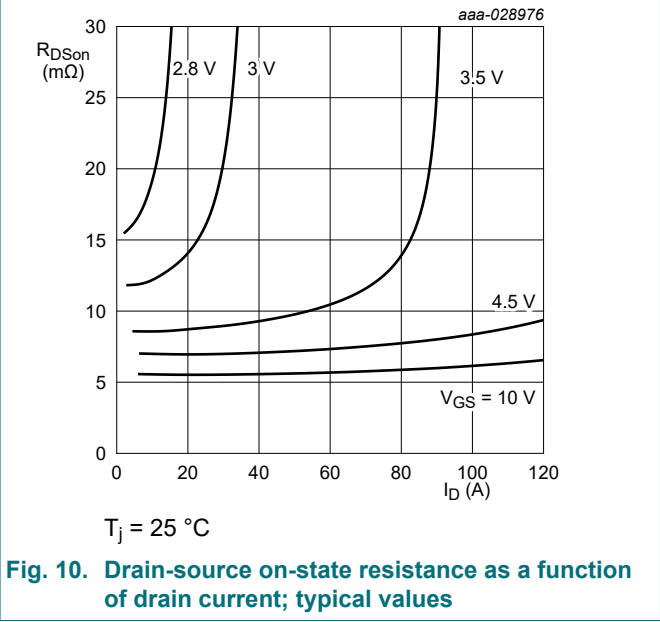
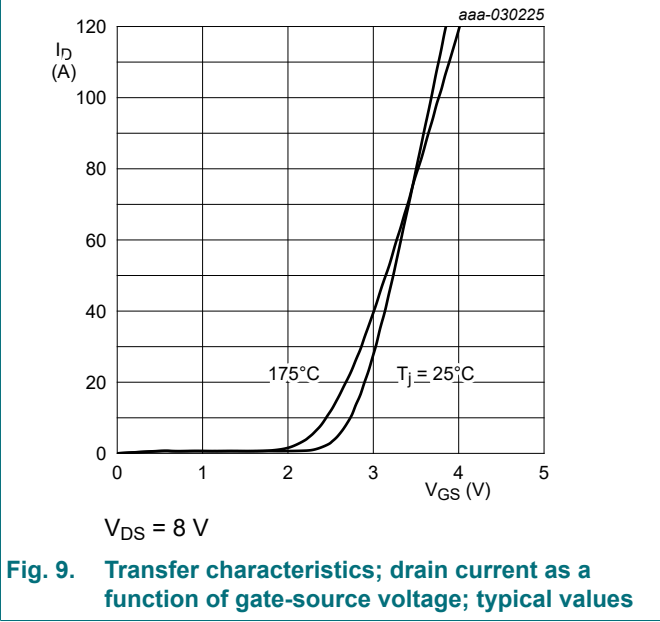
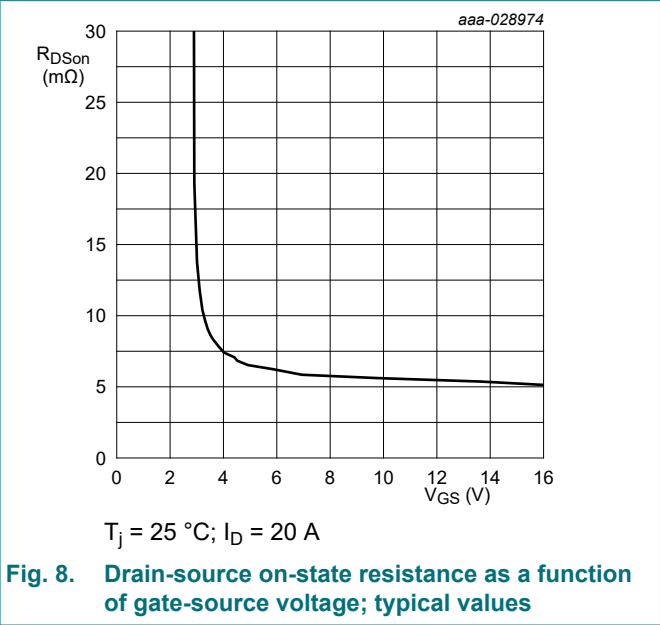
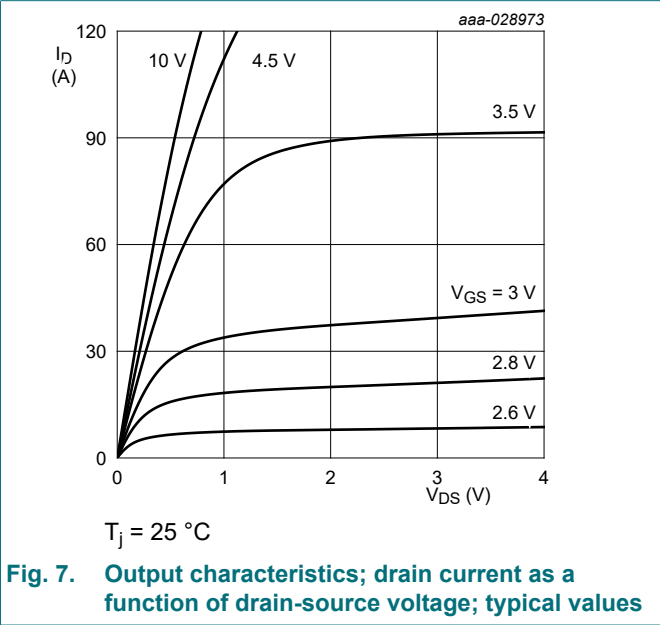
N-channel 40 V, 6.7 mΩ, logic level MOSFET in LPAK33 using NextPower-S3 technology

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ }^\circ\text{C}$	1.45	1.77	2.15	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	$25 \text{ }^\circ\text{C} \leq T_j \leq 150 \text{ }^\circ\text{C}$	-	-4.3	-	mV/K
I_{DSS}	drain leakage current	$V_{DS} = 32 \text{ V}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ }^\circ\text{C}$	-	0.002	1	μA
		$V_{DS} = 32 \text{ V}$; $V_{GS} = 0 \text{ V}$; $T_j = 125 \text{ }^\circ\text{C}$	-	0.77	-	μA
I_{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}$; $V_{DS} = 0 \text{ V}$; $T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
		$V_{GS} = -16 \text{ V}$; $V_{DS} = 0 \text{ V}$; $T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}$; $I_D = 20 \text{ A}$; $T_j = 25 \text{ }^\circ\text{C}$; Fig. 10	-	5.5	6.7	mΩ
		$V_{GS} = 10 \text{ V}$; $I_D = 20 \text{ A}$; $T_j = 175 \text{ }^\circ\text{C}$; Fig. 11	-	-	13	mΩ
		$V_{GS} = 4.5 \text{ V}$; $I_D = 15 \text{ A}$; $T_j = 25 \text{ }^\circ\text{C}$; Fig. 10	-	7	8.6	mΩ
		$V_{GS} = 4.5 \text{ V}$; $I_D = 15 \text{ A}$; $T_j = 175 \text{ }^\circ\text{C}$; Fig. 11	-	-	16.7	mΩ
R_G	gate resistance	$f = 1 \text{ MHz}$; $T_j = 25 \text{ }^\circ\text{C}$	0.3	0.8	1.9	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 20 \text{ A}$; $V_{DS} = 20 \text{ V}$; $V_{GS} = 10 \text{ V}$; Fig. 12 ; Fig. 13	14	22	31	nC
		$I_D = 20 \text{ A}$; $V_{DS} = 20 \text{ V}$; $V_{GS} = 4.5 \text{ V}$; Fig. 12 ; Fig. 13	6.5	10	14	nC
Q_{GS}	gate-source charge		2.4	4.1	6.2	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		1.38	2.3	3.45	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		1.1	1.8	2.7	nC
Q_{GD}	gate-drain charge		0.7	2.5	5	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 20 \text{ A}$; $V_{DS} = 20 \text{ V}$; Fig. 12 ; Fig. 13	-	2.9	-	V
C_{iss}	input capacitance	$V_{DS} = 20 \text{ V}$; $V_{GS} = 0 \text{ V}$; $f = 1 \text{ MHz}$; $T_j = 25 \text{ }^\circ\text{C}$; Fig. 14	961	1479	2071	pF
C_{oss}	output capacitance		280	432	605	pF
C_{rss}	reverse transfer capacitance		18	60	132	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 20 \text{ V}$; $R_L = 1 \text{ } \Omega$; $V_{GS} = 4.5 \text{ V}$; $R_{G(ext)} = 5 \text{ } \Omega$	-	15	-	ns
t_r	rise time		-	21	-	ns
$t_{d(off)}$	turn-off delay time		-	14	-	ns
t_f	fall time		-	10	-	ns
Q_{oss}	output charge	$V_{GS} = 0 \text{ V}$; $V_{DS} = 20 \text{ V}$; $f = 1 \text{ Hz}$; $T_j = 25 \text{ }^\circ\text{C}$	-	13	-	nC
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 20 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ }^\circ\text{C}$; Fig. 15	-	0.85	1.2	V

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Symbol	Parameter	Conditions		Min	Typ	Max	Unit
t_{rr}	reverse recovery time	$I_S = 20\text{ A}$; $dI_S/dt = -100\text{ A}/\mu\text{s}$; $V_{GS} = 0\text{ V}$; $V_{DS} = 20\text{ V}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 16		-	23	-	ns
Q_r	recovered charge		[1]	-	16	-	nC
t_a	reverse recovery rise time			-	14	-	ns
t_b	reverse recovery fall time			-	8.5	-	ns

[1] includes capacitive recovery



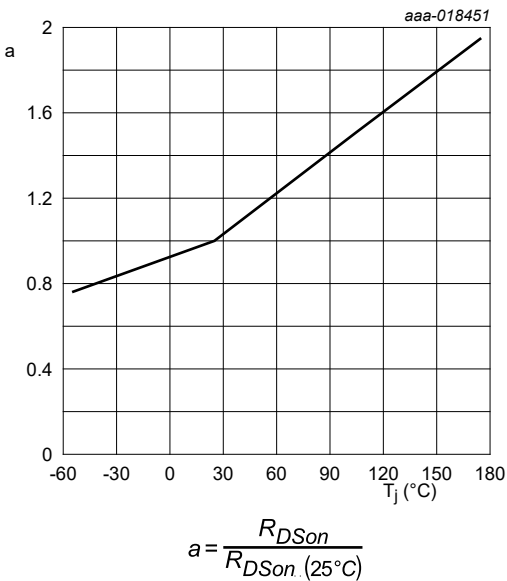


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

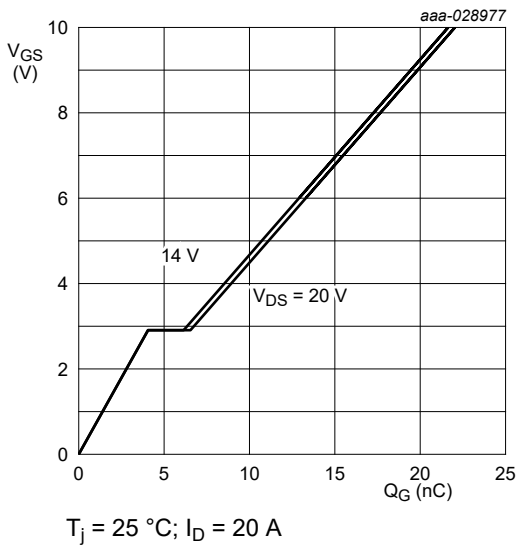


Fig. 12. Gate-source voltage as a function of gate charge; typical values

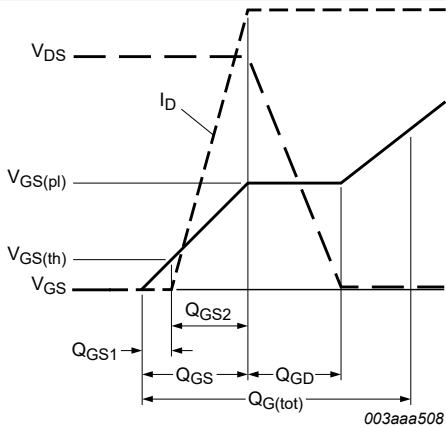


Fig. 13. Gate charge waveform definitions

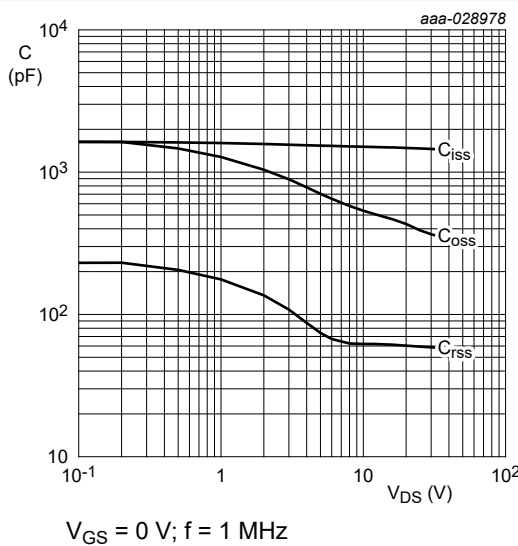
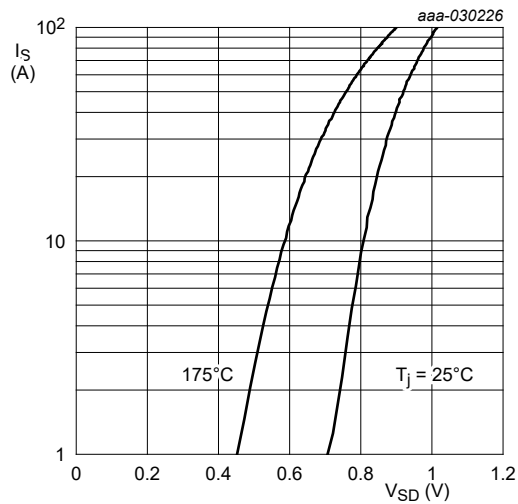


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0\text{ V}$

Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

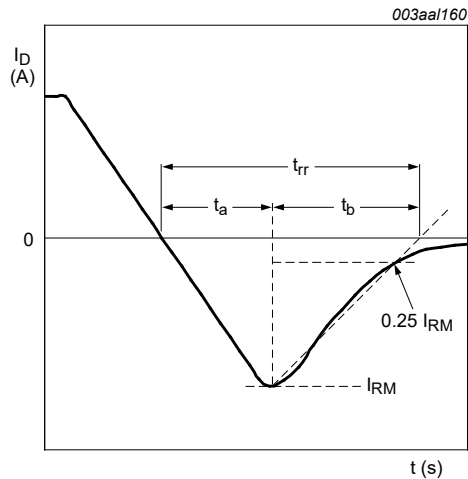


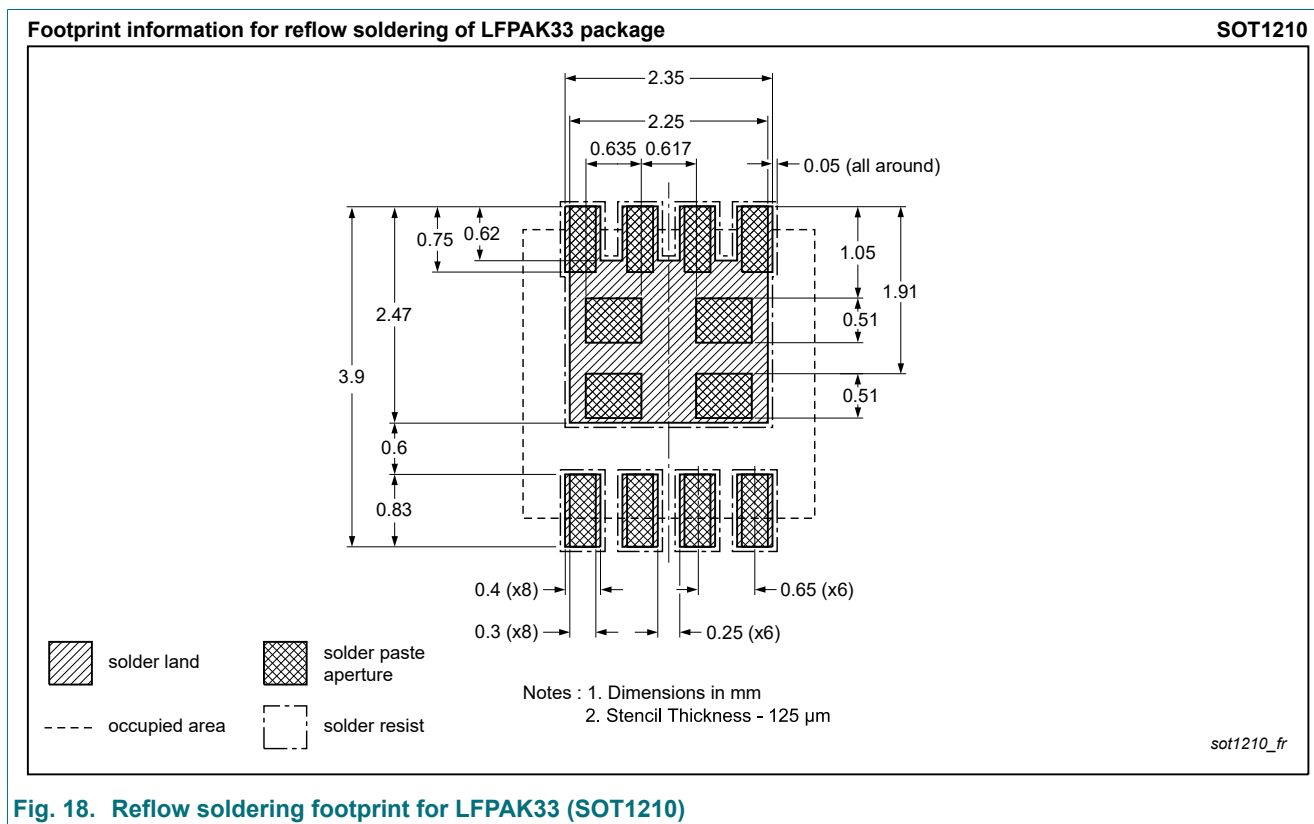
Fig. 16. Reverse recovery timing definition

11. Package outline



Fig. 17. Package outline LPAK33 (SOT1210)

12. Soldering



13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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